

AMENDMENTS

In the Specification

Please replace the paragraph beginning at line 13 of page 11 with the following clean replacement paragraph in accordance with 37 C.F.R. §1.121(b)(1)(ii):

c1 --Such integrated circuitry construction and fabrication methods might be used in a number of different applications, by way of example only in the fabrication of logic or memory circuitry, such as DRAM circuitry fabrication. Fig. 9 illustrates DRAM circuitry and fabrication thereof. A wafer fragment 110 comprises a bulk monocrystalline silicon substrate 112 having a pair of field isolation regions 114. A series of four DRAM word line constructions 116, 117, 118 and 119 are formed over the illustrated substrate, and comprise gates of respective DRAM cell field effect transistors. Gate constructions 116, 117, 118 and 119 are conventional as shown, and comprise a gate dielectric layer (not shown), an overlying conductive polysilicon region, an overlying higher conductive elemental metal or silicide region, and an insulative cap and sidewall spacers, and which are not otherwise specifically identified with numerals. In the illustrated section, word line 117 comprises a transistor access gate having associated source/drain diffusion regions 120 and 122 formed within monocrystalline silicon substrate 12. Similarly, DRAM word line 118 comprises a gate of a DRAM cell field effect transistor having an associated pair of source/drain diffusion regions 122 and 124. Such depicts two DRAM cells which share a

source/drain region 122 which will electrically connect with a bit line, as described subsequently. The other respective source/drain diffusion regions 120 and 124 are formed in electrical connection with DRAM cell capacitor constructions 126 and 127, respectively. The illustrated example is in the fabrication of bit line-over-capacitor DRAM integrated circuitry construction, although other DRAM integrated circuitry and other integrated circuitry constructions and fabrication methods are contemplated.--

Please replace the paragraph beginning at line 21 of page 13 with the following clean replacement paragraph in accordance with 37 C.F.R. §1.121(b)(1)(ii):

--An insulative layer 144 is formed over DRAM capacitor cell electrode layer 140. An example and preferred material is BPSG. A contact opening 146 is formed through insulative layers 144 and 128 for ultimate formation of a conductive bit contact 156. Conductive material 160 is formed within the contact opening in electrical connection with DRAM capacitor cell electrode layer 140 (not shown) and within contact opening 146 in electrical connection with bit contact source/drain diffusion region 122. Conductive material 160 preferably comprises a metal and/or metal compound which is/are capable of oxidizing to a non-conductive metal oxide upon effective exposure to the conductive metal oxide of layer 140. Preferred materials include titanium, titanium nitride, and tungsten, by way of example only. Such layers are deposited and planarized back relative to insulative layer 144 as shown.--

Please replace the paragraph beginning at line 9 of page 14 with the following clean replacement paragraph in accordance with 37 C.F.R. §1.121(b)(1)(ii):

23 --A conductive layer 165 is deposited over and in electrical connection with conductive material 160. Such is patterned to form a DRAM bit line 166 over insulative layer 144 and in electrical connection with source/drain diffusion region 122 through conductive material 160. Other devices might be formed outwardly of layer 165, followed ultimately by formation of a final passivation layer.--

In the Claims

Please replace the claims with the following clean version of the entire set of pending claims, in accordance with 37 C.F.R. § 1.121(c)(1)(i). Cancel all previous versions of any pending claim.

A marked up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. § 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.